

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFSL59N10D

FEATURES

- Static drain-source on-resistance: Ros(on) ≤0.025Ω
- · Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

SYMBOL

VDSS

 V_{GS}

ΙD

IDM

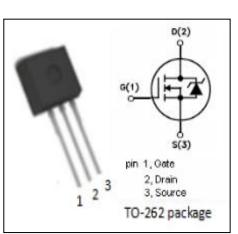
 P_{D}

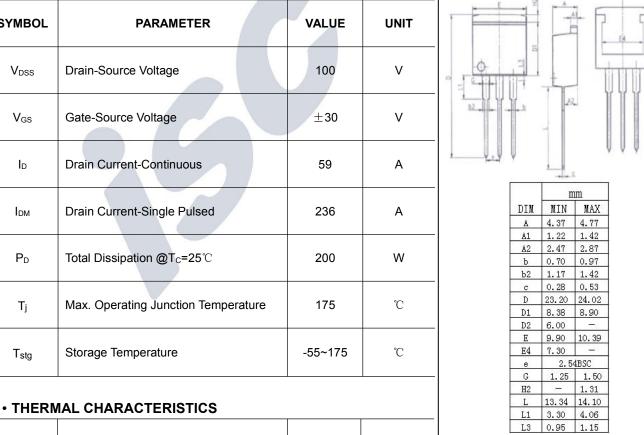
Τi

Tstg

· reliable device for use in a wide variety of applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





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SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.75	°C/W

isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	100			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	3.0		5.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =35.4A			0.025	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±30V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			25	μA
V _{SD}	Diode forward voltage	Is=35.4A, V _{GS} = 0 V			1.3	V



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